

SUBSTRATE PROPERTY	MGGaAs2NSiPE- 500LD	MGGaAs2NSiPP- 500LD	MGGaAs3NSiPE- 500LD	MGGaAs3NSiPP- 500LD	MGGaAs4NSiPE- 500LD	MGGaAs4NSiPP- 500LD
Diameter	2 inch		3 inch		4 inch	
Growth Method	VGF					
Conduction Type	n-type					
Dopant	Si (Silicon)					
Crystal Orientation	(100)2°/6°/15° off (110)					
Carrier Concentration	(0.4~2.5)E18 cm ⁻³					
Resistivity at RT	(1.5~9)E-3 Ω·cm					
Mobility	1500-3000 cm ² /V·sec					
Etch Pit Density	<500cm ⁻²					
Surface Finish	P/E	P/P	P/E	P/P	P/E	P/P
Thickness	220~350 um					
Applications	Laser Diodes					

*The other specifications can be customized according to customer's requirements